

# LN65

## GaAs Infrared Light Emitting Diode

For optical control systems

### ■ Features

- High-power output, high-efficiency:  $P_O = 5.5$  mW (typ.)
- Good radiant power output linearity with respect to input current
- Suited for use in high-speed modulation
- Infrared light emission close to monochromatic light:  $\lambda_p = 950$  nm (typ.)

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Power dissipation	$P_D$	160	mW
Forward current	$I_F$	100	mA
Pulse forward current *	$I_{FP}$	1.5	A
Reverse voltage	$V_R$	3	V
Operating ambient temperature	$T_{opr}$	-25 to +85	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-40 to +100	$^\circ\text{C}$

Note) \*:  $f = 100$  Hz, Duty cycle = 0.1%

### ■ Electro-Optical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

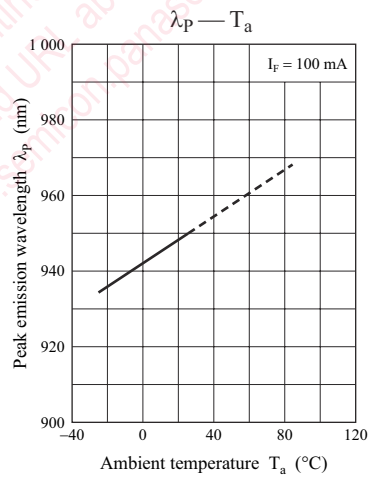
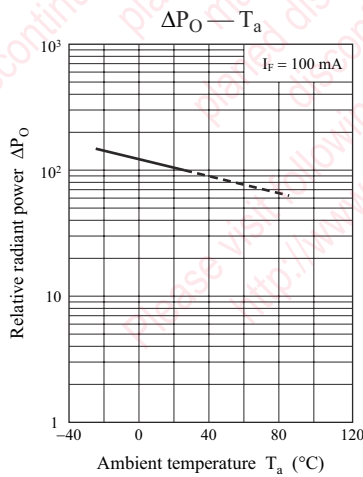
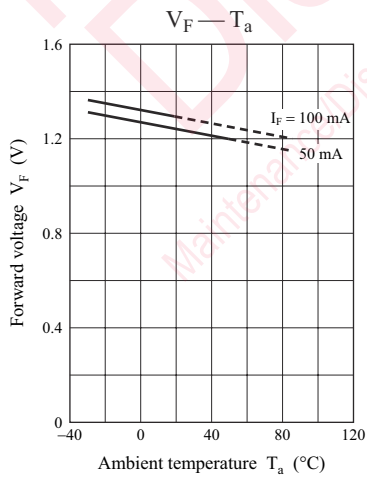
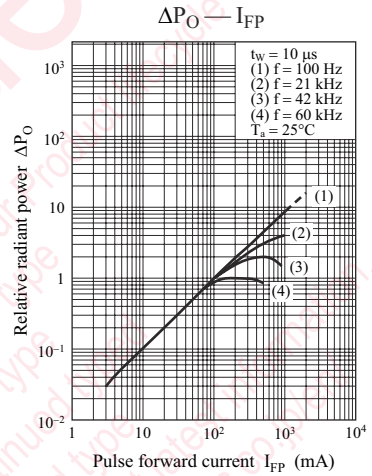
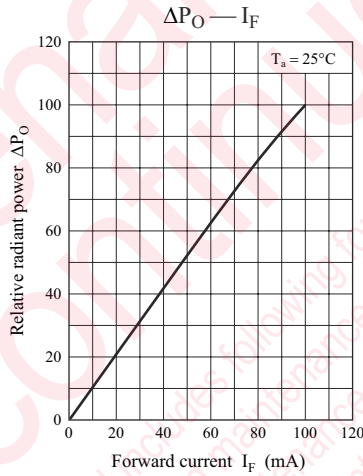
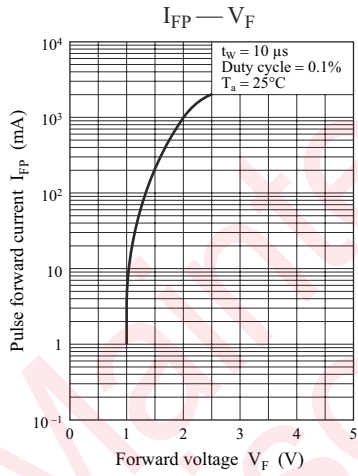
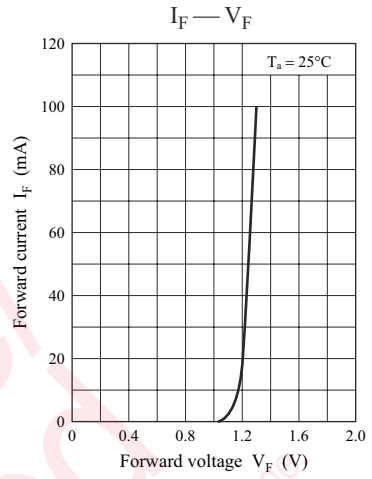
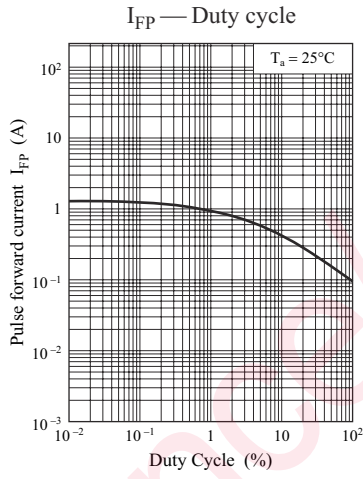
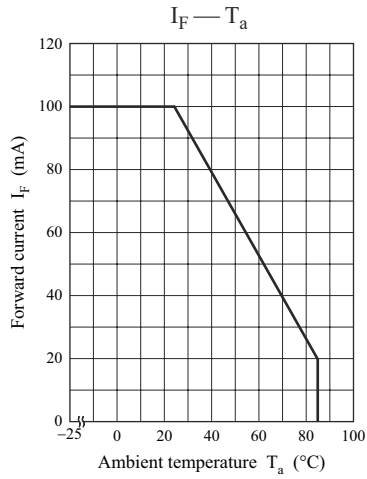
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Radiant power *	$P_O$	$I_F = 100$ mA	4.3	5.5		mW
Reverse current	$I_R$	$V_R = 3$ V			10	$\mu\text{A}$
Forward voltage	$V_F$	$I_F = 100$ mA		1.3	1.6	V
Terminal capacitance	$C_t$	$V_R = 0$ V, $f = 1$ MHz		50		pF
Peak emission wavelength	$\lambda_p$	$I_F = 100$ mA		950		nm
Spectral half band width	$\Delta\lambda$	$I_F = 100$ mA		50		nm
Half-power angle	$\theta$	The angle when the radiant power is halved.		35		$^\circ$

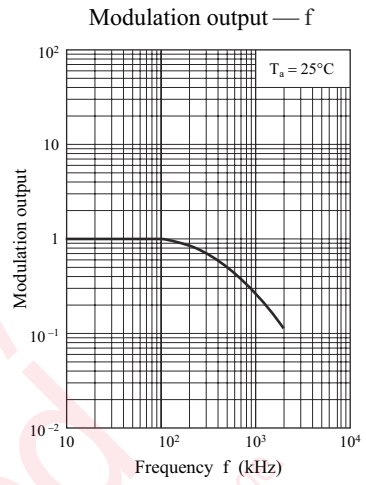
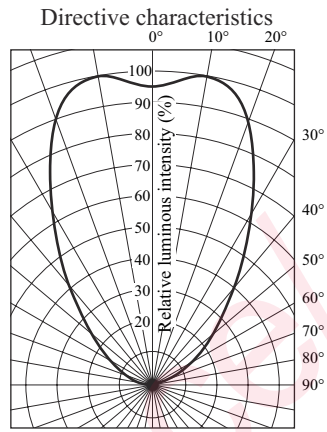
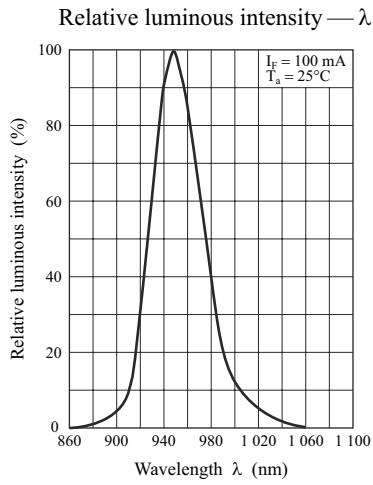
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 measuring methods for diodes.

2. Cutoff frequency: 1 MHz

$$f_c : 10 \times \log \frac{P_O \text{ at } f = f_c}{P_O \text{ at } f = 50 \text{ kHz}} = -3$$

3. \*: A light detection element uses a silicon diode have proofread a load with a standard device.





Maintenance/Discontinued

Maintenance/Discontinued includes following four Product lifecycle stage

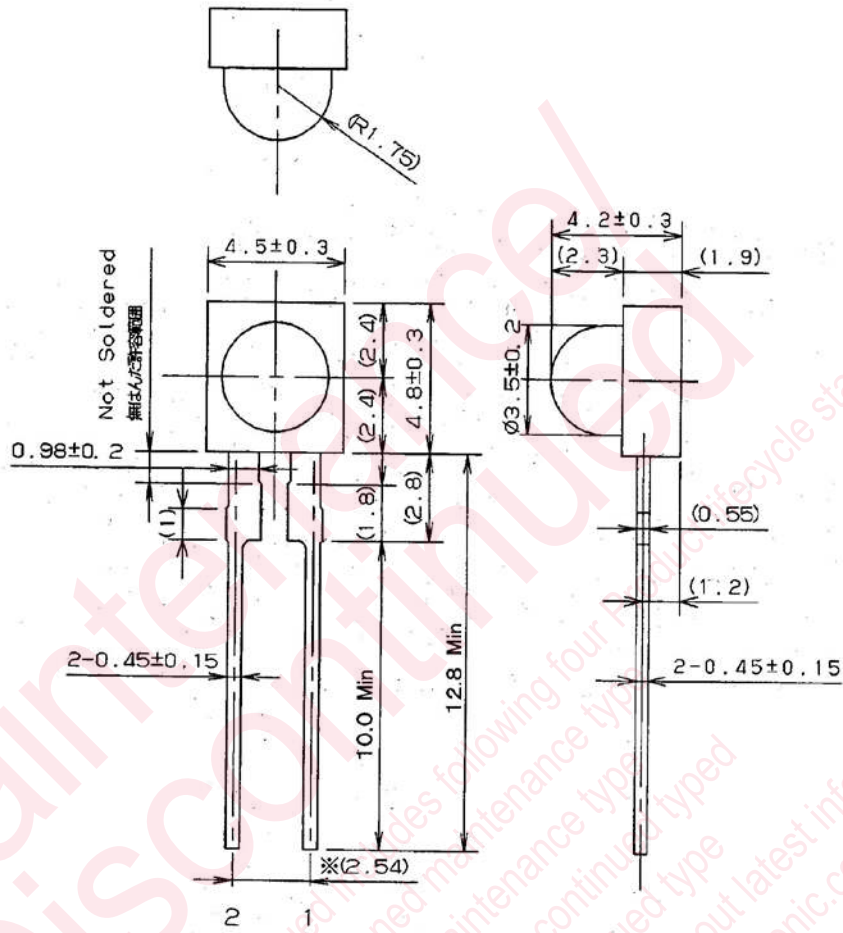
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- maintenace type
- planned discontinued type
- discontinued type

Please visit following URL about latest information.

http://www.semicon.panasonic.co.jp/en/

■ Package (Unit: mm)

LETLSN2S0002



- Pin name
- 1: Anode
- 2: Cathode

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